

AMENDMENTS TO THE SPECIFICATION

Please amend the paragraph bridging pages 4-5 with the following amended paragraph:

Conventionally, the p-conduction-type GaN semiconductor layer for fabricating a pn-junction gallium nitride-based semiconductor light-emitting device is formed through addition of an element belonging to Group II of the periodic table serving as a p-type impurity (i.e., Group II impurity). For example, there has been disclosed a technique in which a Group II impurity, such as magnesium (Mg) or zinc (Zn), is added to a GaN layer through ion injection means (see, for example, ~~JP-A SHO 51-71590~~ JP-A SHO 54-71590).